

TOSHIBA FIELD EFFECT TRANSISTOR SILICON N CHANNEL MOS TYPE (U-MOS)

2SK2466

HIGH SPEED, HIGH CURRENT SWITCHING APPLICATIONS

CHOPPER REGULATOR, DC-DC CONVERTER AND MOTOR DRIVE APPLICATIONS

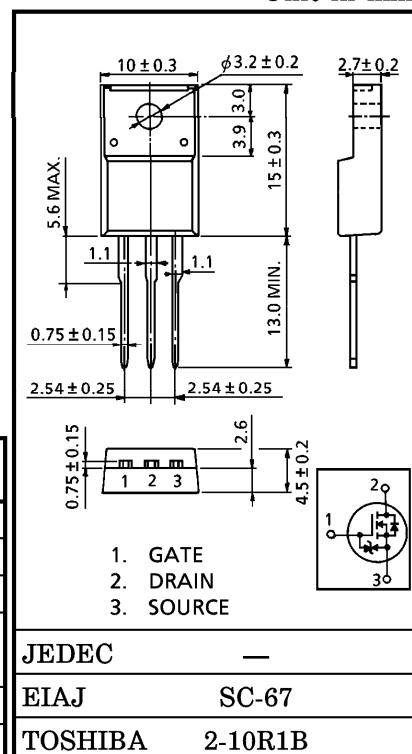
INDUSTRIAL APPLICATIONS

Unit in mm

- 4 V Gate Drive
- Low Drain-Source ON Resistance : $R_{DS(ON)} = 34 \text{ m}\Omega$ (Typ.)
- High Forward Transfer Admittance : $|Y_{fs}| = 30 \text{ S}$ (Typ.)
- Low Leakage Current : $I_{DSS} = 100 \mu\text{A}$ (Max.) ($V_{DS} = 100 \text{ V}$)
- Enhancement-Mode : $V_{th} = 0.8 \sim 2.0 \text{ V}$
($V_{DS} = 10 \text{ V}$, $I_D = 1 \text{ mA}$)

MAXIMUM RATINGS ($T_a = 25^\circ\text{C}$)

CHARACTERISTIC		SYMBOL	RATING	UNIT
Drain-Source Voltage		V_{DSS}	100	V
Drain-Gate Voltage ($R_{GS} = 20 \text{ k}\Omega$)		V_{DGR}	100	V
Gate-Source Voltage		V_{GSS}	± 20	V
Drain Current	DC	I_D	30	A
	Pulse	I_{DP}	120	
Drain Power Dissipation ($T_c = 25^\circ\text{C}$)		P_D	40	W
Single Pulse Avalanche Energy**		E_{AS}	293	mJ
Avalanche Current		I_{AR}	30	A
Repetitive Avalanche Energy*		E_{AR}	4	mJ
Channel Temperature		T_{ch}	150	$^\circ\text{C}$
Storage Temperature Range		T_{stg}	$-55 \sim 150$	$^\circ\text{C}$



Weight : 1.9 g

THERMAL CHARACTERISTICS

CHARACTERISTIC	SYMBOL	MAX.	UNIT
Thermal Resistance, Channel to Case	$R_{th(ch-c)}$	3.125	$^\circ\text{C/W}$
Thermal Resistance, Channel to Ambient	$R_{th(ch-a)}$	62.5	$^\circ\text{C/W}$

Note ;

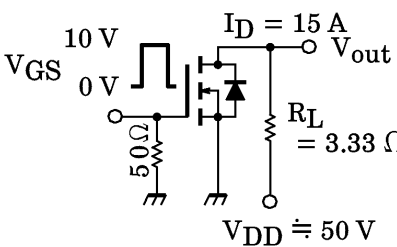
* Repetitive rating ; Pulse Width Limited by Max. junction temperature.

** $V_{DD} = 25 \text{ V}$, $T_{ch} = 25^\circ\text{C}$ (initial), $L = 525 \mu\text{H}$, $R_G = 25 \Omega$, $I_{AR} = 30 \text{ A}$ **This transistor is an electrostatic sensitive device.****Please handle with caution.**

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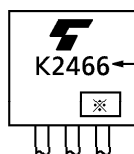
ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Gate Leakage Current		I_{GSS}	$V_{GS} = \pm 16 \text{ V}, V_{DS} = 0 \text{ V}$	—	—	± 20	μA
Drain Cut-off Current		I_{DSS}	$V_{DS} = 100 \text{ V}, V_{GS} = 0 \text{ V}$	—	—	100	μA
Drain-Source Breakdown Voltage		$V_{(BR) DSS}$	$I_D = 10 \text{ mA}, V_{GS} = 0 \text{ V}$	100	—	—	V
Gate Threshold Voltage		V_{th}	$V_{DS} = 10 \text{ V}, I_D = 1 \text{ mA}$	0.8	—	2.0	V
Drain-Source ON Resistance		$R_{DS(ON)}$	$V_{GS} = 4 \text{ V}, I_D = 15 \text{ A}$	—	40	70	$\text{m}\Omega$
			$V_{GS} = 10 \text{ V}, I_D = 15 \text{ A}$	—	34	46	
Forward Transfer Admittance		$ Y_{fs} $	$V_{DS} = 10 \text{ V}, I_D = 15 \text{ A}$	13	30	—	S
Input Capacitance		C_{iss}	$V_{DS} = 10 \text{ V}, V_{GS} = 0 \text{ V},$ $f = 1 \text{ MHz}$	—	3250	—	pF
Reverse Transfer Capacitance		C_{rss}		—	230	—	
Output Capacitance		C_{oss}		—	520	—	
Switching Time	Rise Time	t_r	 $V_{IN} : t_r, t_f < 5 \text{ ns},$ $\text{Duty} \leq 1\%, t_w = 10 \mu\text{s}$	—	33	—	ns
	Turn-on Time	t_{on}		—	60	—	
	Fall Time	t_f		—	95	—	
	Turn-off Time	t_{off}		—	230	—	
Total Gate Charge (Gate-Source Plus Gate-Drain)		Q_g	$V_{DD} \doteq 80 \text{ V}, V_{GS} = 10 \text{ V},$ $I_D = 30 \text{ A}$	—	68	—	nC
Gate-Source Charge		Q_{gs}		—	46	—	
Gate-Drain ("Miller") Charge		Q_{gd}		—	22	—	

SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Continuous Drain Reverse Current	I_{DR}	—	—	—	30	A
Pulse Drain Reverse Current	I_{DRP}	—	—	—	120	A
Diode Forward Voltage	V_{DSF}	$I_{DR} = 30 \text{ A}, V_{GS} = 0 \text{ V}$	—	—	-1.7	V
Reverse Recovery Time	t_{rr}	$I_{DR} = 30 \text{ A}, V_{GS} = 0 \text{ V}$	—	120	—	ns
Reverse Recovery Charge	Q_{rr}	$dI_{DR} / dt = 50 \text{ A} / \mu\text{s}$	—	280	—	nC

MARKING



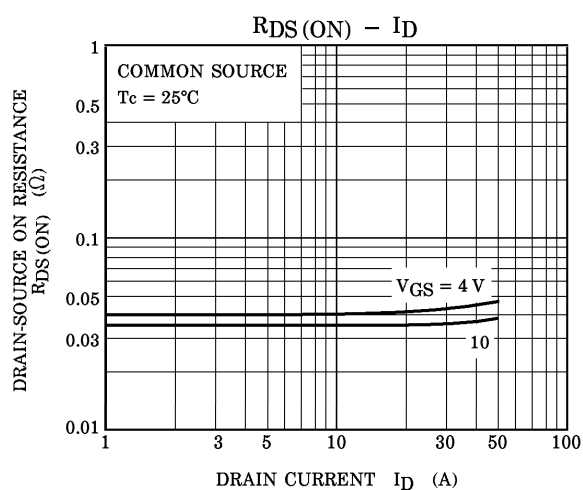
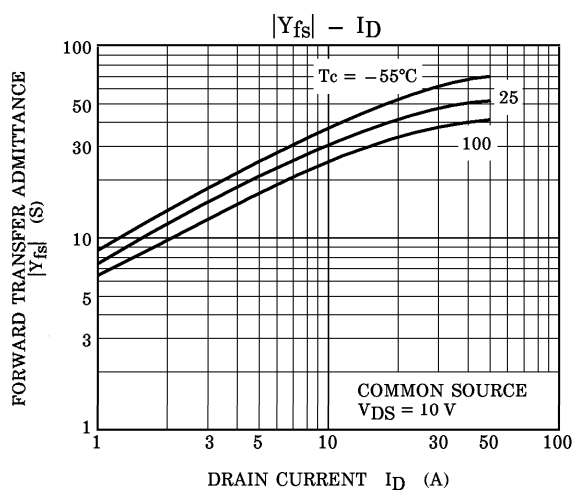
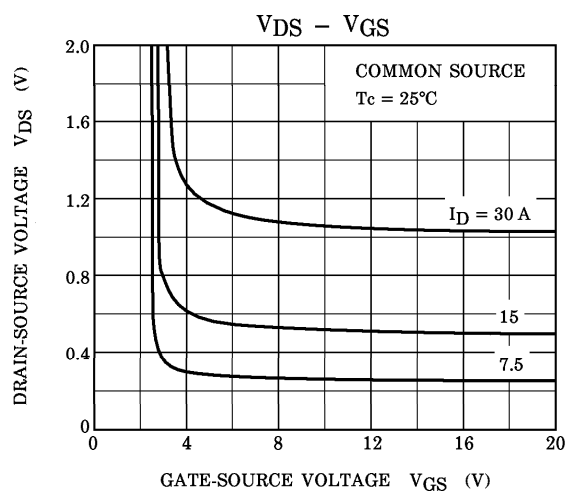
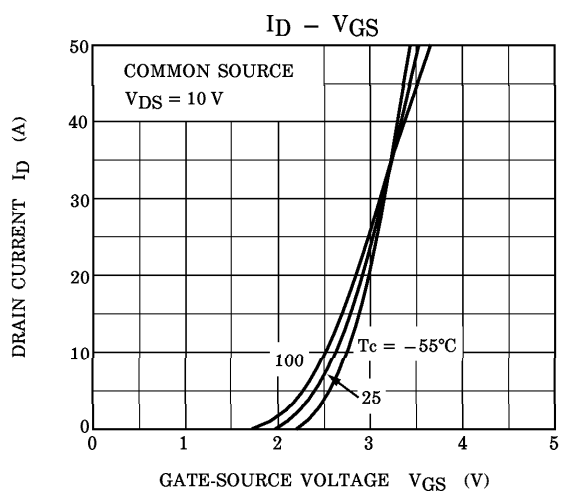
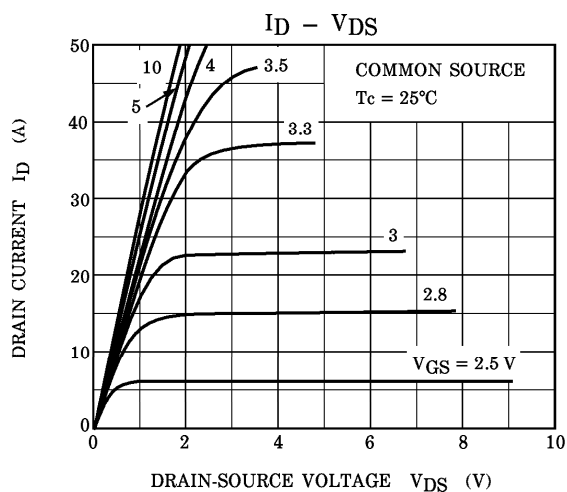
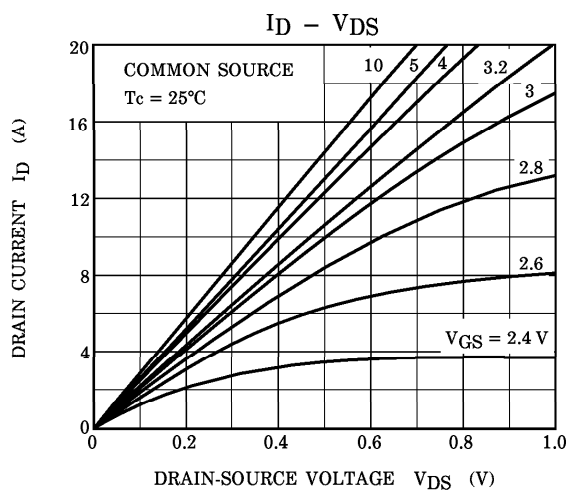
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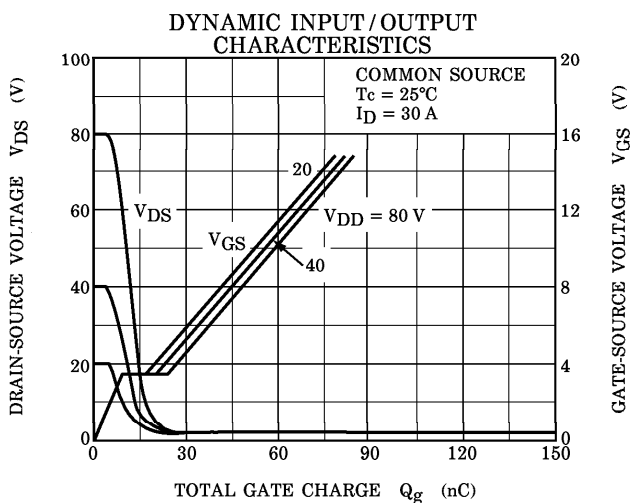
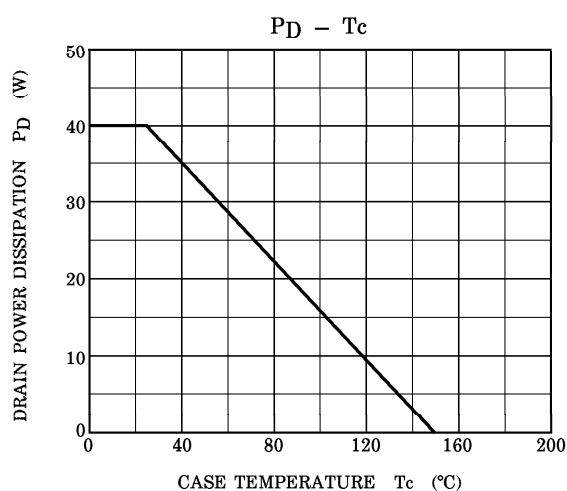
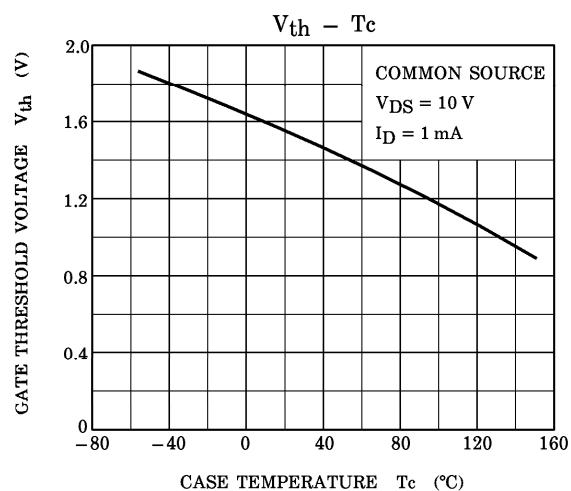
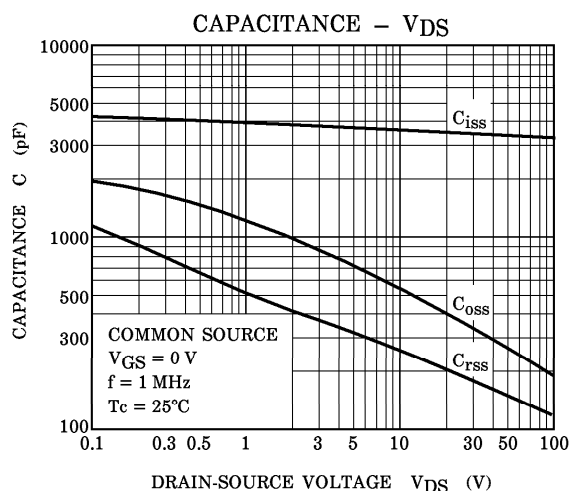
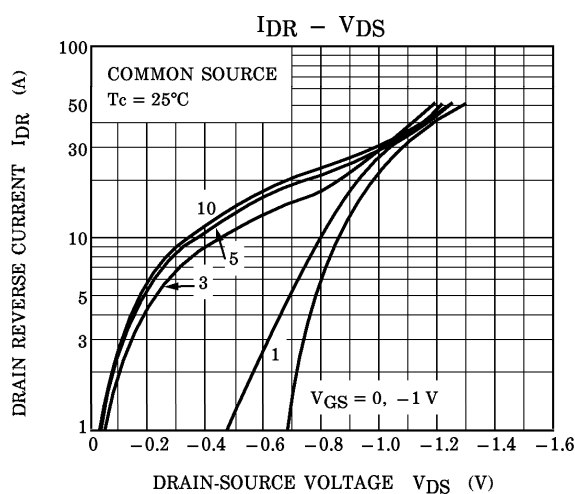
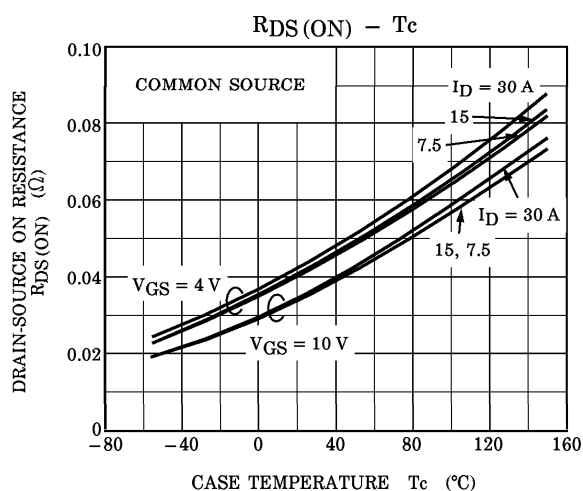
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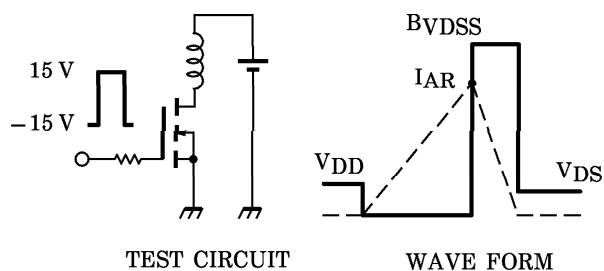
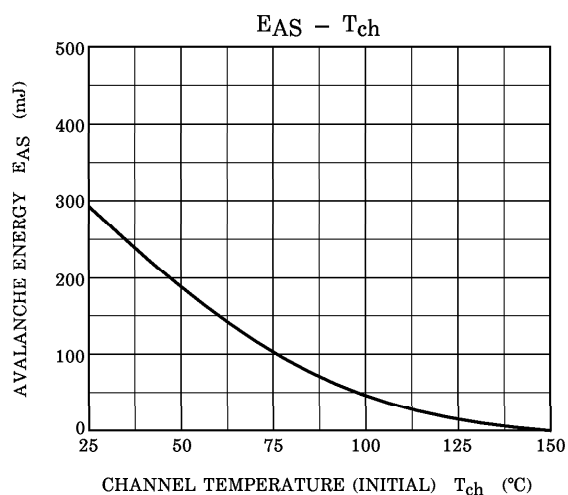
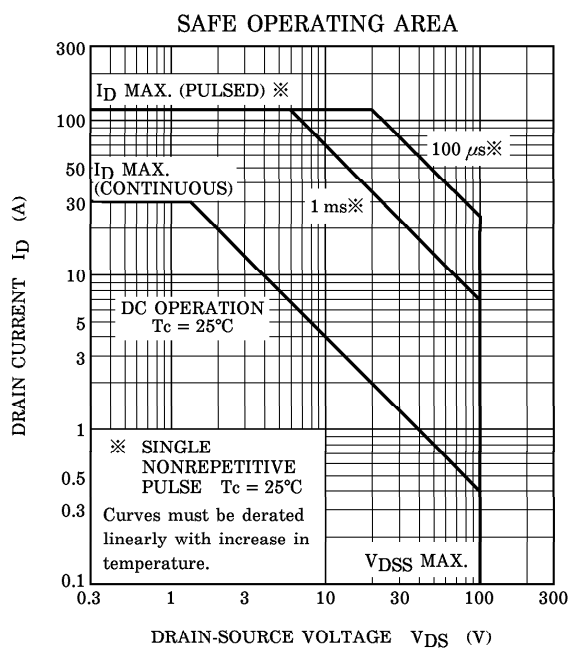
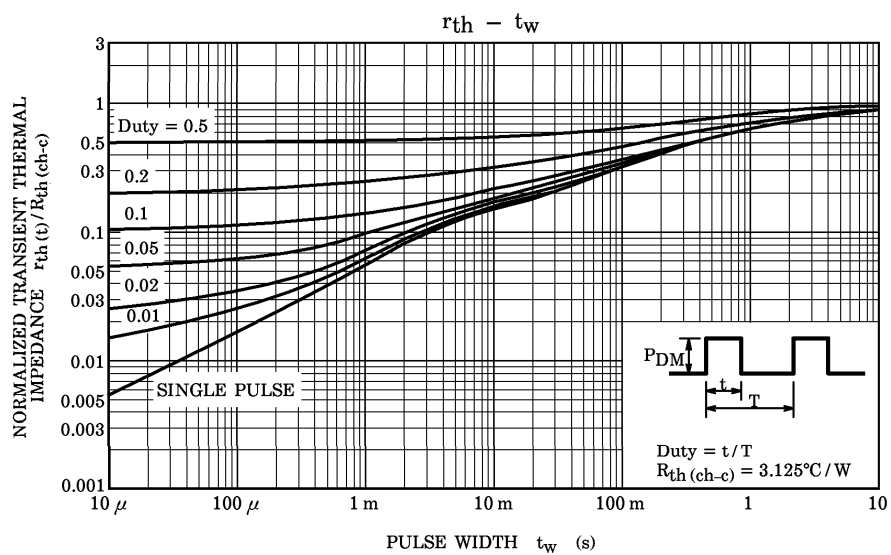


Month (Starting from Alphabet A)

Year (Last Number of the Christian Era)







$$\text{Peak } I_{AR} = 30 \text{ A, } R_G = 25 \, \Omega, \quad E_{AS} = \frac{1}{2} \cdot L \cdot I^2 \cdot \left(\frac{B_{V_{DS}}}{B_{V_{DS}} - V_{DD}} \right)$$

$$V_{DD} = 25 \text{ V, } L = 525 \, \mu\text{H}$$